

Mark: 3R

## **PNP Switching Transistor**

This device is designed for very high speed saturated switching at collector currents to 100 mA. Sourced from Process 65. See PN4258 for characteristics.

#### Absolute Maximum Ratings\* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	15	V
V <sub>CBO</sub>	Collector-Base Voltage	15	V
V <sub>EBO</sub>	Emitter-Base Voltage	4.5	V
Ic	Collector Current - Continuous	200	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

### NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

## Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max		Units
		2N5771	*MMBT5771	
P <sub>D</sub>	Total Device Dissipation	350	225	mW
	Derate above 25°C	2.8	1.8	mW/∘C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125		°C/W
$R_{ ext{ hetaJA}}$	Thermal Resistance, Junction to Ambient	357	556	°C/W

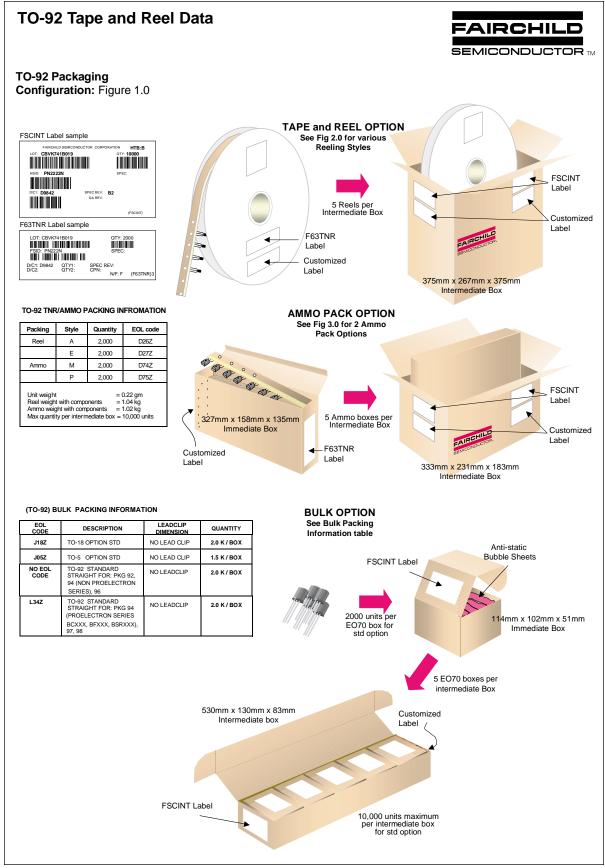
\*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

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# PNP Switching Transistor (continued)

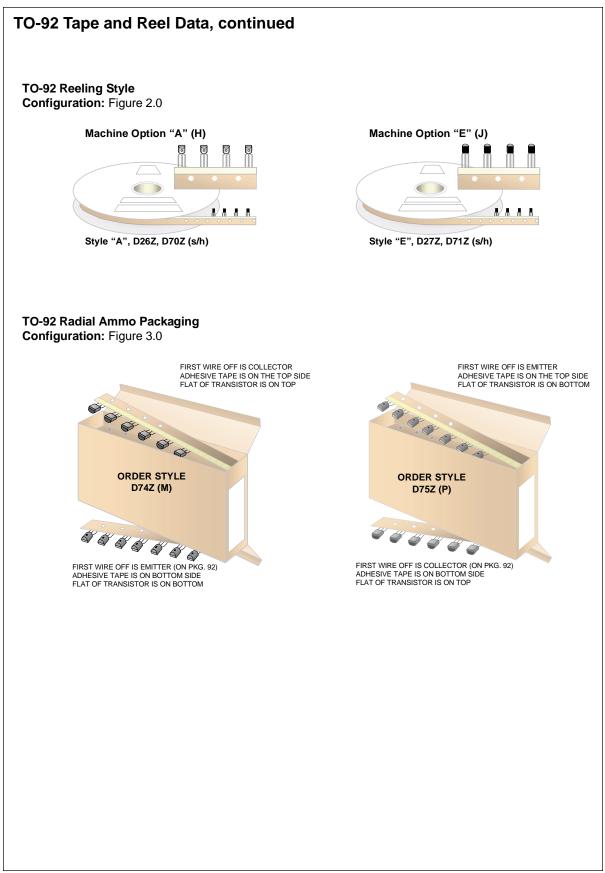
Symbol	Parameter	Test Conditions	Min	Max	Units
				1	
	RACTERISTICS				
/ <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 3.0 \text{ mA}, I_{\rm B} = 0$	15		V
(BR)CES	Collector-Emitter Breakdown Voltage	$I_{C} = 100 \ \mu A, \ V_{BE} = 0$	15		V
(BR)CBO	Collector-Base Breakdown Voltage	$I_{C} = 100 \ \mu A, \ I_{E} = 0$	15		V
(BR)EBO	Emitter-Base Breakdown Voltage	$I_{E} = 100 \ \mu A, \ I_{C} = 0$	4.5		V
во	Collector Cutoff Current	$V_{CB} = 8.0 \text{ V}, I_E = 0$		10	nA
ES	Collector Cutoff Current	$V_{CE} = 8.0 \text{ V}, V_{BE} = 0$		10	nA
BO	Emitter Cutoff Current	$V_{CE} = 8.0 \text{ V}, V_{BE} = 0, T_A = 125^{\circ}\text{C}$ $V_{EB} = 4.5 \text{ V}, I_C = 0$		5.0 1.0	μΑ μΑ
во		$V_{EB} = 4.0 V, V_{C} = 0$		1.0	μΛ
N CHAR	ACTERISTICS*				
FE	DC Current Gain	$I_{C} = 1.0 \text{ mA}, V_{CE} = 0.5 \text{ V}$	35		
		$I_{\rm C} = 10$ mA, $V_{\rm CE} = 0.3$ V	50	120	
		$I_{C} = 10mA, V_{CE} = 0.3V, T_{A} = -55^{\circ}C$ $I_{C} = 50 mA, V_{CE} = 1.0 V$	20 40		
CE(sat)	Collector-Emitter Saturation Voltage	$I_{\rm C} = 1.0 \text{ mA}, V_{\rm CE} = 1.0 \text{ V}$	40	0.15	V
oc(out)		$I_{\rm C} = 10$ mA, $I_{\rm B} = 1.0$ mA		0.18	V
	Dage Emitter Seturation Voltage	$I_{\rm C} = 50 \text{ mA}, I_{\rm B} = 5.0 \text{ mA}$		0.6	V
BE(sat)	Base-Emitter Saturation Voltage	$I_{C} = 1.0 \text{ mA}, I_{B} = 0.1 \text{ mA}$ $I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA}$	0.75	0.8 0.95	V
		$I_{\rm C} = 50$ mA, $I_{\rm B} = 5.0$ mA		1.5	V
	GNAL CHARACTERISTICS				
cb	Collector-Base Capacitance	$V_{CB} = 5.0 \text{ V}, I_E = 0,$		3.0	pF
<b>`</b>	Emitter Rase Canacitance	f = 140  kHz $V_{BE} = 0.5 \text{ V}, I_C = 0,$		3.5	۶E
eb	Emitter-Base Capacitance	$v_{BE} = 0.5 \text{ V}, I_C = 0,$ f = 140 kHz		3.5	pF
fe	Small-Signal Current Gain	$I_{C} = 10 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 100 MHz	8.5		MHz
				I	
	NG CHARACTERISTICS Storage Time	$I_{\rm C} = 10 \text{ mA}, V_{\rm CC} = 1.5 \text{ V},$		20	ns
	Storage Time	$I_{B1} = I_{B2} = 1.0 \text{ mA}$		20	115
n	Turn-On Time	$I_{\rm C}$ = 10 mA, $V_{\rm CC}$ = 1.5 V,		15	ns
off	Turn-Off Time	$I_B = 1.0 \text{ mA}$ $I_C = 10 \text{ mA}, V_{CC} = 1.5 \text{ V},$		20	ns
		$I_{B1} = I_{B2} = 1.0 \text{ mA}$			
Pulse Test: P	ulse Width $\leq$ 300 $\mu s$ , Duty Cycle $\leq$ 2.0%				
NOTE: All volta	ages (V) and currents (A) are negative polarity for PNP t	ransistors.			

2N5771 / MMBT5771

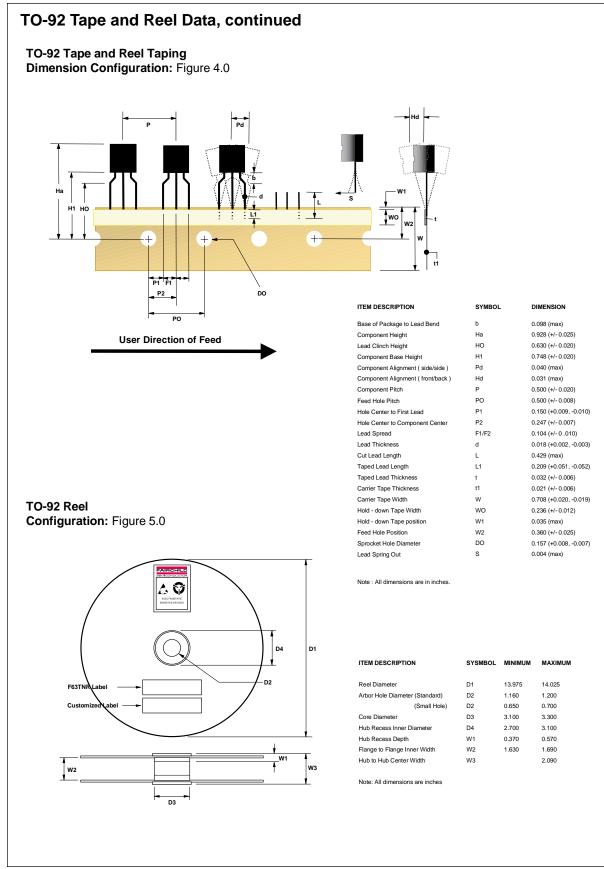


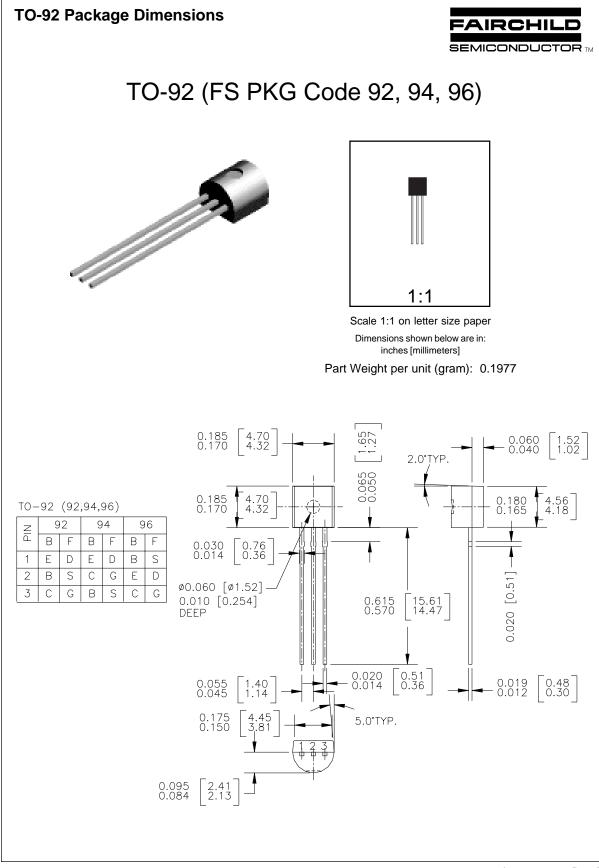
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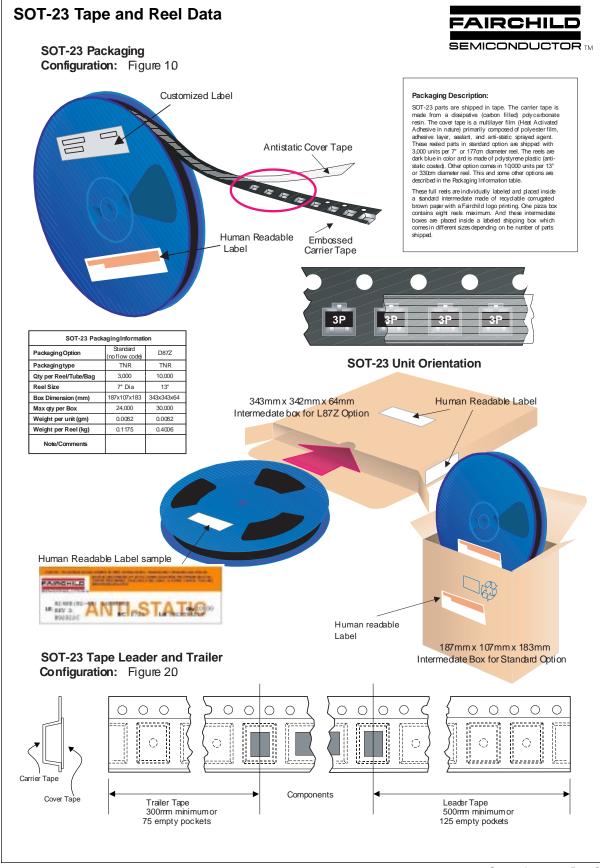
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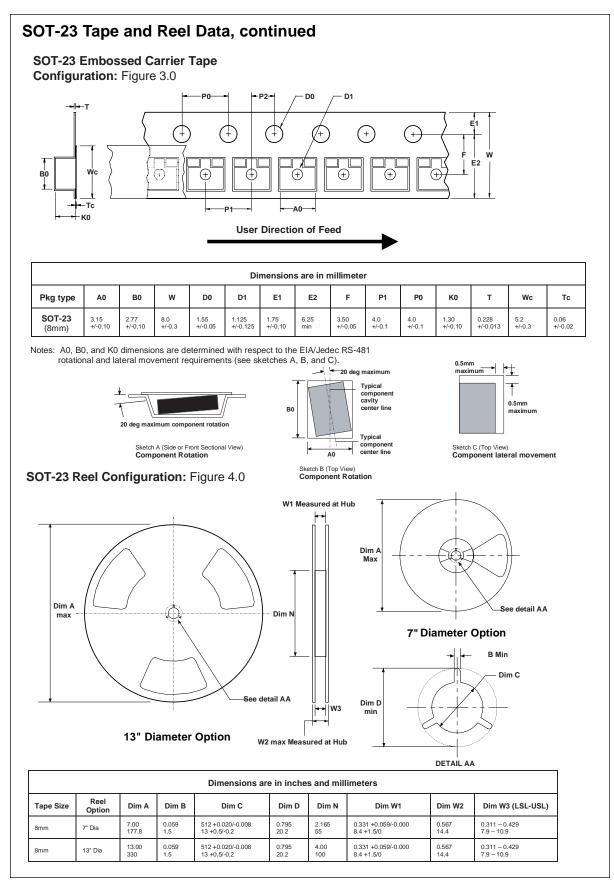
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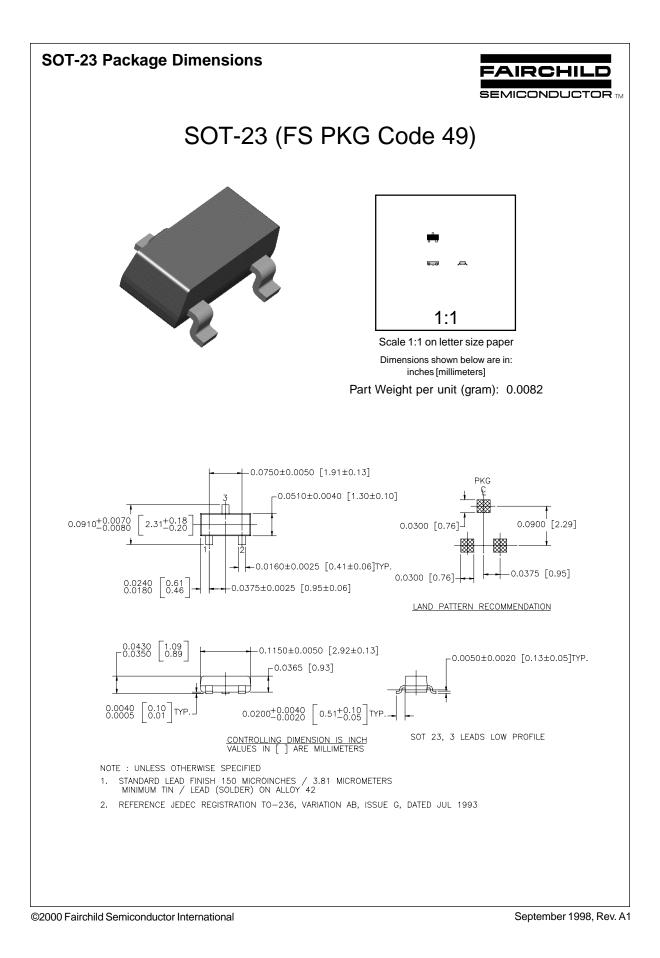


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